



Advanced Analog Circuits

Preliminary Datasheet

3A DDR TERMINATION REGULATOR

AP2302

General Description

The AP2302 linear regulator is designed to meet the JEDEC specification SSTL-2 and SSTL-18 for termination of DDR-SDRAM. The regulator can sink or source up to 3A current continuously, offers enough current for most DDR applications. Output voltage is designed to track the reference voltage within a 2% (DDR I) and 3% (DDR II) tolerance for load regulation while preventing shooting through on the output stage. On-chip thermal limiting provides protection against a combination of high current and ambient temperature which would create an excessive junction temperature.

The AP2302, used in conjunction with series termination resistors, provides an excellent voltage source for active termination schemes of high speed transmission lines as those seen in high speed memory buses and distributed backplane designs.

The AP2302 is available in SOIC-8, TO-252-5L and TO-263-5L packages.

Features

- Support Both DDR I ($1.25V_{TT}$) and DDR II ($0.9V_{TT}$) Requirements
- Source and Sink Current up to 3A
- High Accuracy Output Voltage at Full-load
- Adjustable V_{OUT} by External Resistors
- Shutdown for Standby or Suspend Mode Operation with High-impedance Output

Applications

- DDR-SDRAM Termination
- DDR-II Termination
- SSTL-2 Termination



Figure 1. Package Types of AP2302



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Pin Configuration

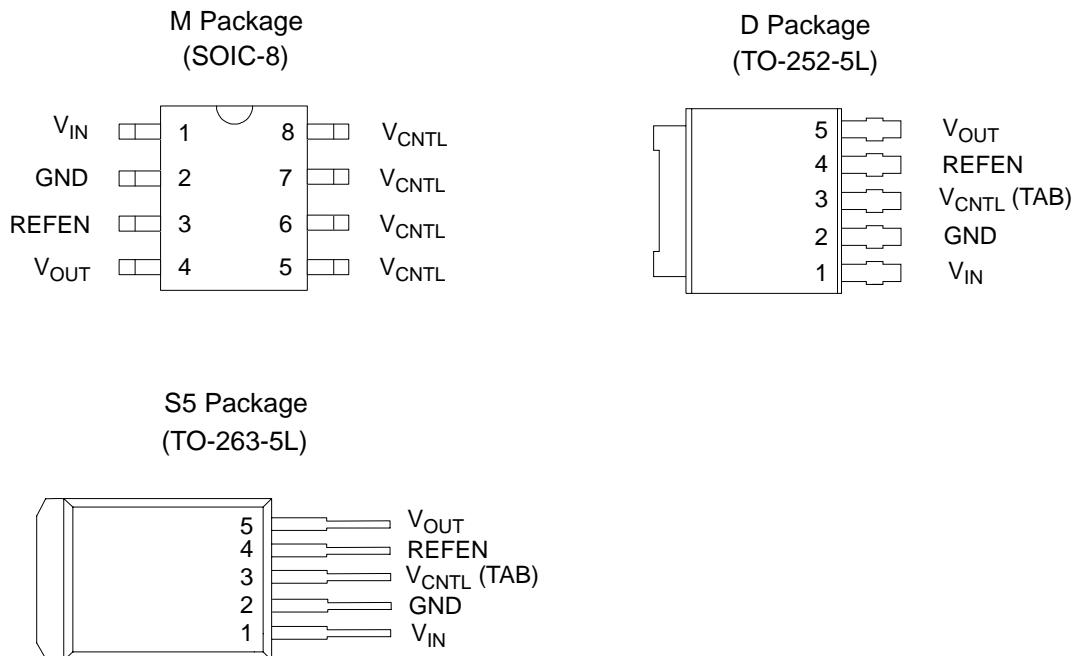


Figure 2. Pin Configuration of AP2302 (Top View)

Pin Description

| Pin Number | | | Pin Name | Function |
|------------|-----------|-----------|------------|--|
| SOIC-8 | TO-252-5L | TO-263-5L | | |
| 1 | 1 | 1 | V_{IN} | Power Input |
| 2 | 2 | 2 | GND | Ground |
| 3 | 4 | 4 | REFEN | Reference Voltage Input and Chip Enable |
| 4 | 5 | 5 | V_{OUT} | Output Voltage |
| 5, 6, 7, 8 | 3 | 3 | V_{CNTL} | Supply Voltage for Internal Circuit (Internally Connected for SOIC-8), (TAB for TO-252-5L and TO-263-5L) |



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Functional Block Diagram

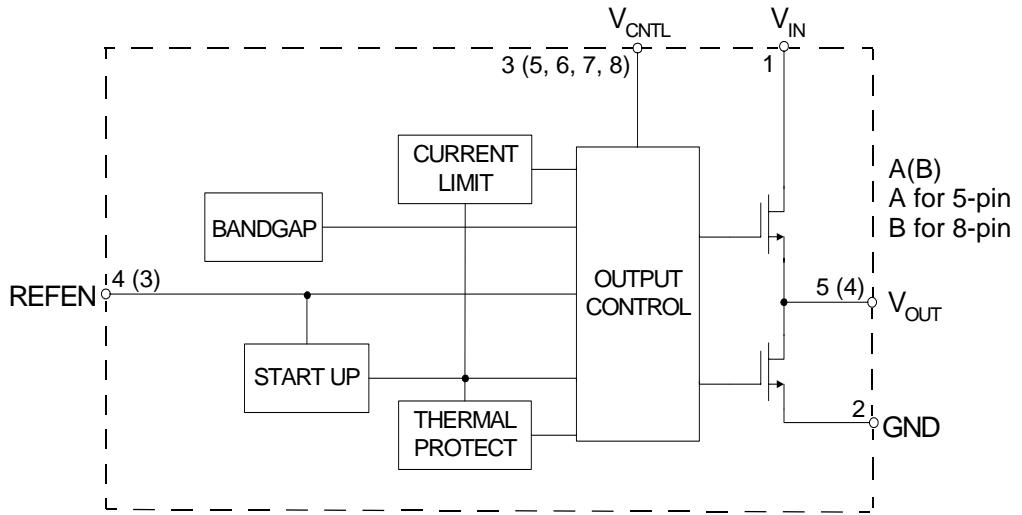
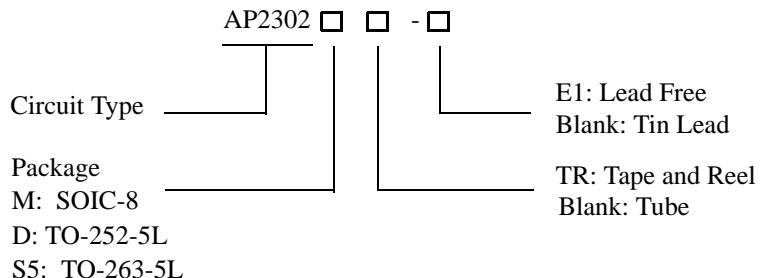


Figure 3. Functional Block Diagram of AP2302

Ordering Information



| Package | Temperature Range | Part Number | | Marking ID | | Packing Type |
|-----------|-------------------|-------------|---------------|------------|-------------|--------------|
| | | Tin Lead | Lead Free | Tin Lead | Lead Free | |
| SOIC-8 | 0 to 125°C | AP2302M | AP2302M-E1 | 2302M | 2302M-E1 | Tube |
| | | AP2302MTR | AP2302MTR-E1 | 2302M | 2302M-E1 | Tape & Reel |
| TO-252-5L | 0 to 125°C | AP2302D | AP2302D-E1 | AP2302D | AP2302D-E1 | Tube |
| | | AP2302DTR | AP2302DTR-E1 | AP2302D | AP2302D-E1 | Tape & Reel |
| TO-263-5L | 0 to 125°C | AP2302S5 | AP2302S5-E1 | AP2302S5 | AP2302S5-E1 | Tube |
| | | AP2302S5TR | AP2302S5TR-E1 | AP2302S5 | AP2302S5-E1 | Tape & Reel |

BCD Semiconductor's Pb-free products, as designated with "E1" suffix in the part number, are RoHS compliant.



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Absolute Maximum Ratings (Note 1)

| Parameter | Symbol | Value | | Unit |
|---------------------------------------|-------------------|----------------------------------|------------------|------|
| Supply Voltage for Internal Circuit | V _{CNTL} | 7 | | V |
| Power Dissipation | P _D | Internally Limited | | W |
| ESD (Human Body Model) | ESD | 2 | | kV |
| Junction Temperature | T _J | 150 | | °C |
| Storage Temperature Range | T _{STG} | -65 to 150 | | °C |
| Lead Temperature (Soldering, 10sec) | T _{LEAD} | 260 | | °C |
| Package Thermal Resistance (Free Air) | θ _{JA} | SOIC-8 TO-252-5L TO-263-5L | 160 130 90 | °C/W |

Note 1: Stresses greater than those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "Recommended Operating Conditions" is not implied. Exposure to "Absolute Maximum Ratings" for extended periods may affect device reliability.

Recommended Operating Conditions

| Parameter | Symbol | Min | Typ | Max | Unit |
|-------------------------------------|-------------------------------|-----|-----|-------------------|------|
| Supply Voltage for Internal Circuit | V _{CNTL} (Note 2, 3) | | 3.3 | 6 | V |
| Power Input | DDR I | 1.6 | 2.5 | V _{CNTL} | V |
| | DDR II | | 1.8 | | |
| Junction Temperature | T _J | 0 | | 125 | °C |

Note 2: Keep V_{CNTL} \geq V_{IN} in power on and power off sequences.

Note 3: For safe operation, V_{CNTL} MUST be tied to 3.3V rather than 5V.



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Electrical Characteristics

(T_J=25°C, V_{IN}=2.5V, V_{CNTL}=3.3V, V_{REFEN}=1.25V, C_{OUT}=10μF (Ceramic), unless otherwise specified.)

| Parameter | Symbol | Conditions | Min | Typ | Max | Unit |
|--|--------------------|--|-----|-----|-----|------|
| Output Offset Voltage | V _{OS} | I _L =0A (Note 4) | -20 | 0 | 20 | mV |
| Load Regulation | DDR I | I _L =0 to 1.5A | | 0.8 | 2 | % |
| | | I _L =0 to -1.5A | | 0.8 | 2 | |
| | DDR II | I _L =0 to 1.5A | | 1.2 | 3 | |
| | | I _L =0 to -1.5A | | 1.2 | 3 | |
| Quiescent Current of V _{CNTL} | I _Q | No Load | | 3 | 5 | mA |
| Leakage Current in Shutdown Mode | I _{SHDN} | V _{REFEN} <0.2V, R _L =180Ω | | 3 | 6 | μA |
| Protection | | | | | | |
| Current Limit | I _{LIMIT} | | 3 | | | A |
| Thermal Shutdown Temperature | T _{SHDN} | 3.3V≤V _{CNTL} ≤5V | | 150 | | °C |
| Thermal Shutdown Hysteresis | | | | 50 | | °C |
| Shutdown Function | | | | | | |
| Shutdown Threshold Trigger | | Output=High | 0.8 | | | V |
| | | Output=Low | | | 0.2 | |

Note 4: V_{OS} is the voltage measurement defined as V_{OUT} subtracted from V_{REFEN}.



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Typical Performance Characteristics

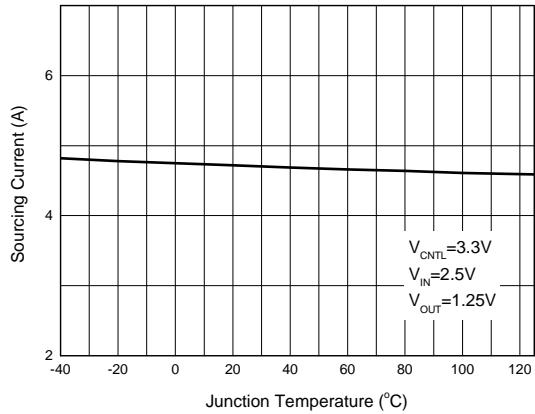


Figure 4. Sourcing Current vs. Junction Temperature

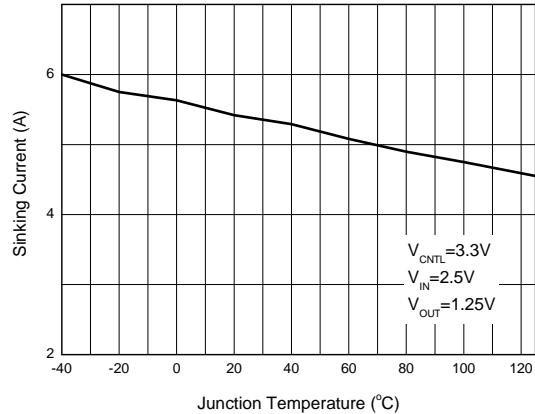


Figure 5. Sinking Current vs. Junction Temperature

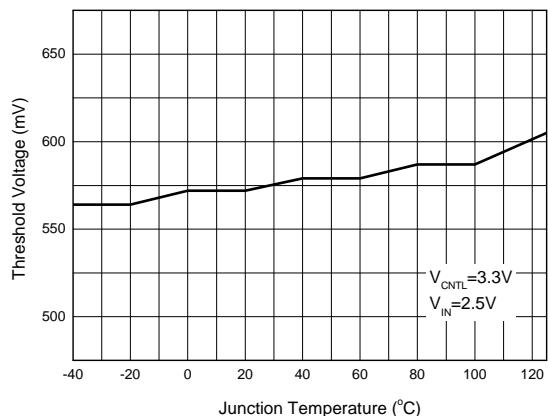


Figure 6. Threshold Voltage vs. Junction Temperature

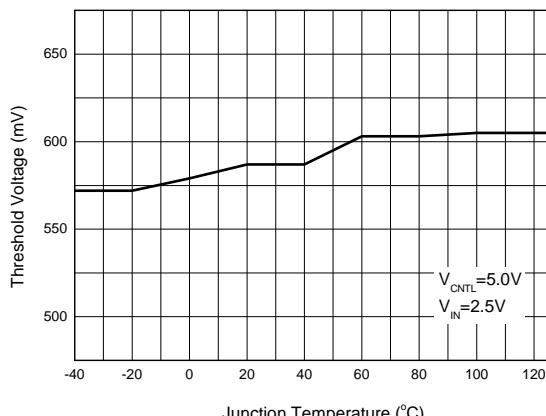


Figure 7. Threshold Voltage vs. Junction Temperature



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Typical Performance Characteristics (Continued)

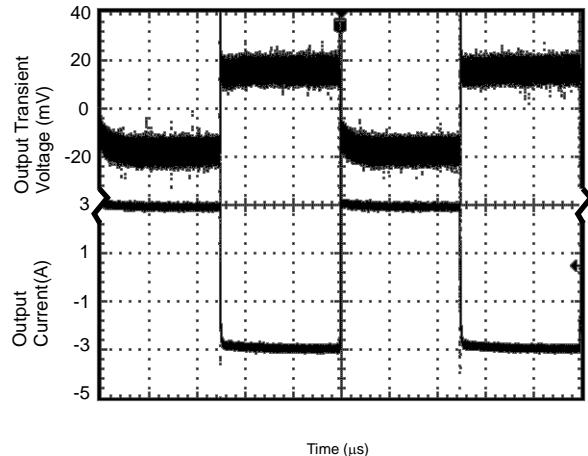


Figure 8. $0.9V_{TT}$ at 3A Transient Response
(Conditions: $V_{IN}=2.5V$, $V_{CNTL}=3.3V$, $C_{OUT}=10\mu F$)

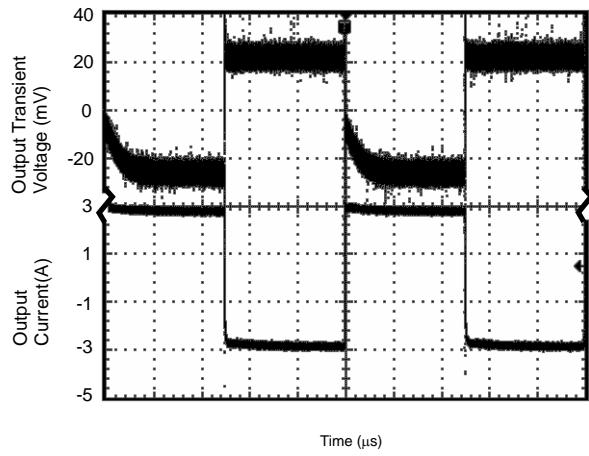


Figure 9. $1.25V_{TT}$ at 3A Transient Response
(Conditions: $V_{IN}=2.5V$, $V_{CNTL}=3.3V$, $C_{OUT}=10\mu F$)

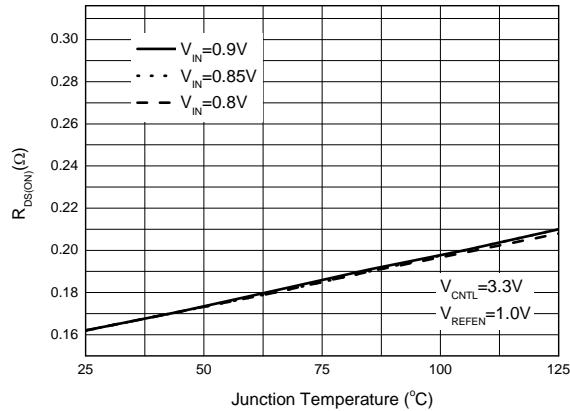


Figure 10. $R_{DS(on)}$ vs. Junction Temperature

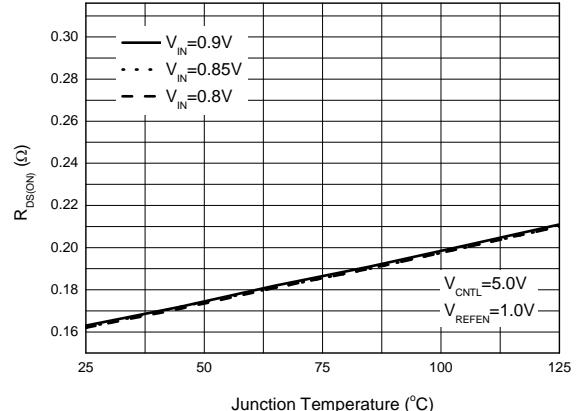


Figure 11. $R_{DS(on)}$ vs. Junction Temperature



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Typical Performance Characteristics (Continued)

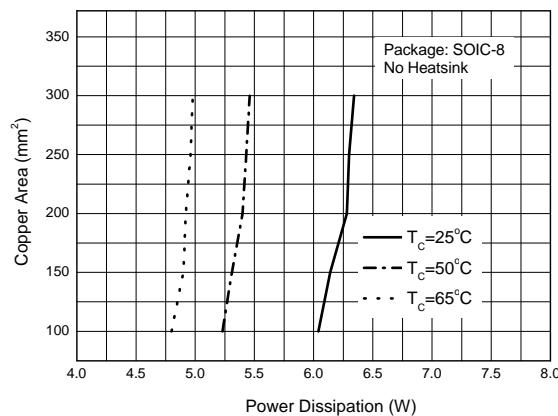


Figure 12. Copper Area vs. Power Dissipation

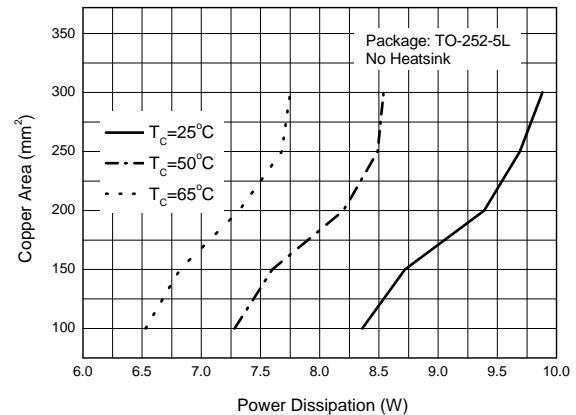


Figure 13. Copper Area vs. Power Dissipation

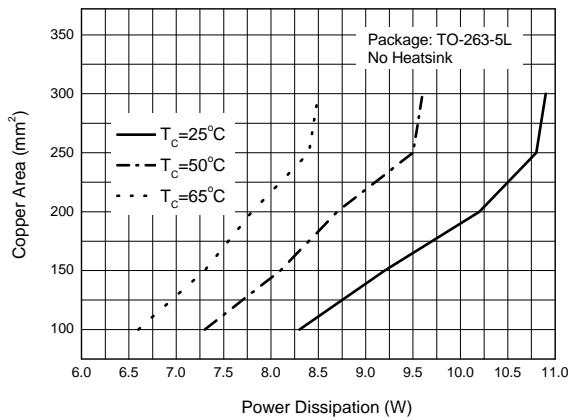


Figure 14. Copper Area vs. Power Dissipation



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Typical Application

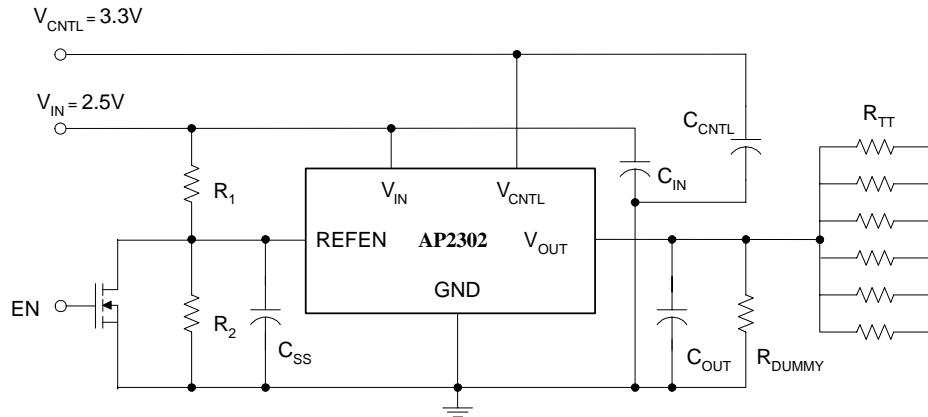


Figure 15. Typical Application of AP2302

R₁=R₂=100KΩ, R_{TT}=50Ω / 33Ω / 25Ω

R_{DUMMY}=1KΩ, as for V_{OUT} discharge when V_{IN} is not present but V_{CNTL} is present

C_{SS}=1μF, C_{IN}=470μF, C_{CNTL}=47μF, C_{OUT}=470μF



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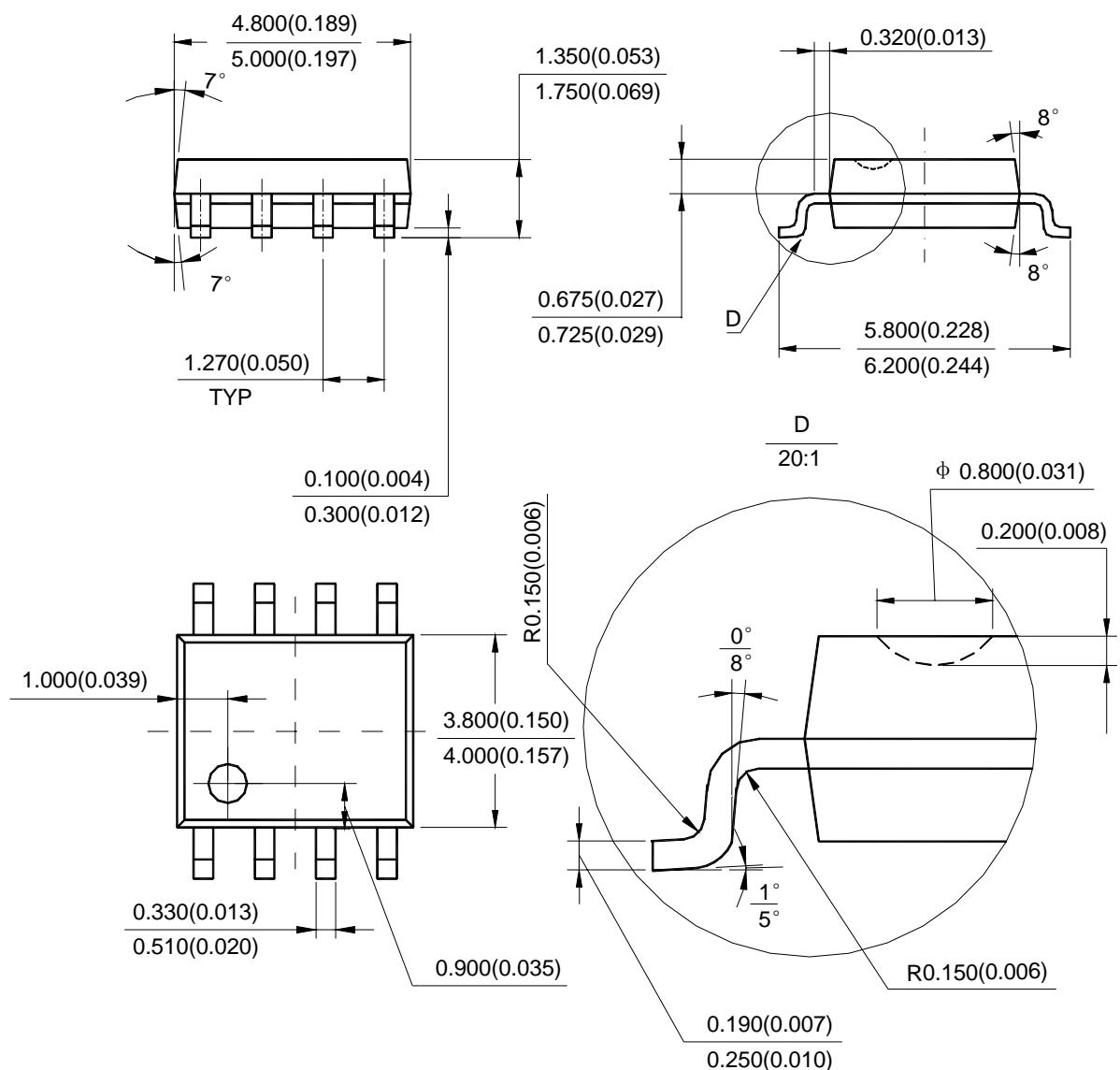
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Mechanical Dimensions

SOIC-8

Unit: mm(inch)





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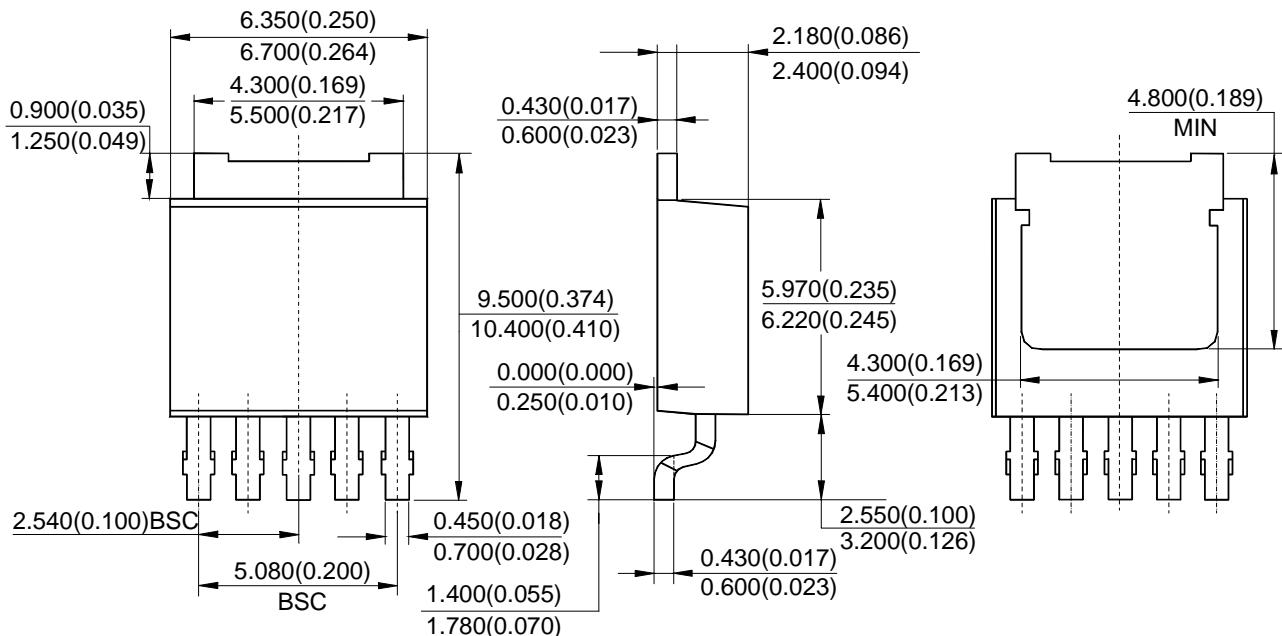
3A DDR TERMINATION REGULATOR

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Mechanical Dimensions (Continued)

TO-252-5L

Unit: mm(inch)





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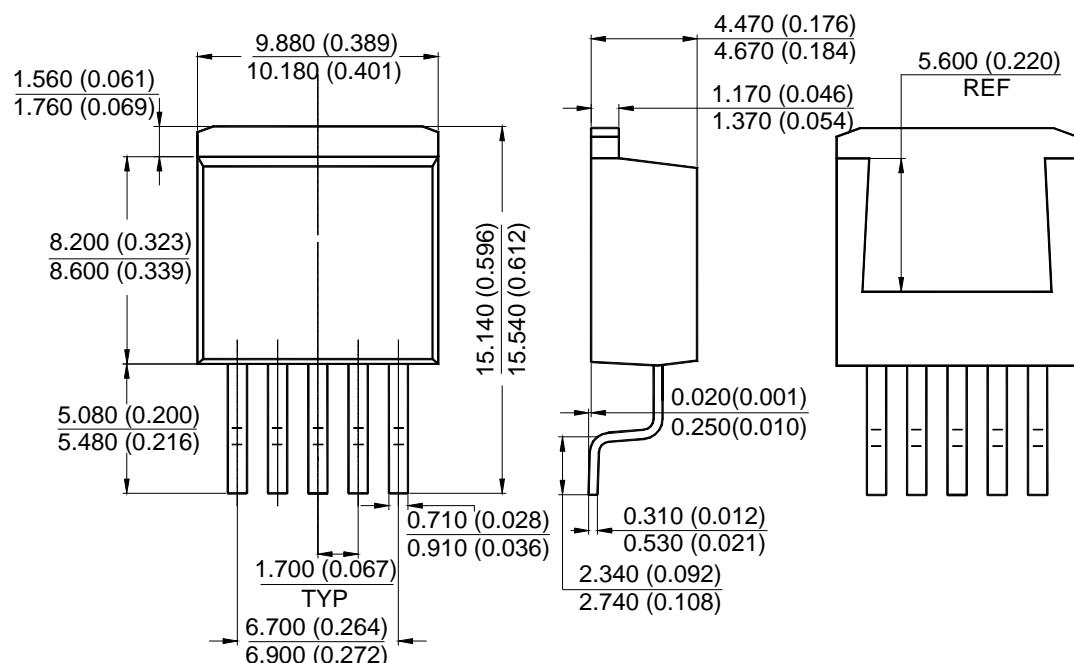
3A DDR TERMINATION REGULATOR

AP2302

Mechanical Dimensions (Continued)

TO-263-5L

Unit: mm(inch)





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